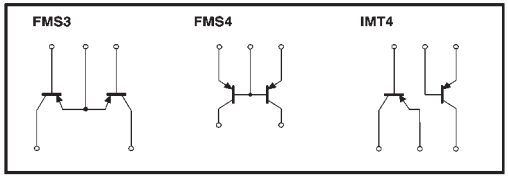
General purpose (dual transistors)

FMS3 / FMS4 / IMT4

●**Features**

1) Two 2SA1514K chips in an SMT package.
2) High breakdown voltage.

●**Circuit diagrams**



●**Absolute maximum ratings** (Ta=25℃)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	−120	V	
Collector-emitter voltage	V_{CEO}	−120	V	
Emitter-base voltage	V_{EBO}	−5	V	
Collector current	I_C	−50	mA	
Power dissipation	Pc	300 (TOTAL)	mW	*
Junction temperature	Tj	150	℃	
Storage temperature	Tstg	−55～+150	℃	

* 200mW per element must not be exceeded.

●**Package, marking, and packaging specifications**

Part No.	FMS3	FMS4	IMT4
Package	SMT5	SMT5	SMT6
Marking	S3	S4	T4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

●**Electrical characteristics** (Ta=25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	−120	—	—	V	I_C=−50 μA
Collector-emitter breakdown voltage	BV_{CEO}	−120	—	—	V	I_C=−1mA
Emitter-base breakdown voltage	BV_{EBO}	−5	—	—	V	I_E=−50 μA
Collector cutoff current	I_{CBO}	—	—	−0.5	μA	V_{CB}=−100V
Emitter cutoff current	I_{EBO}	—	—	−0.5	μA	V_{EB}=−4V
DC current transfer ratio	h_{FE}	180	—	820	—	V_{CE}=−6V, I_C=−2mA
Transition frequency	f_T	—	140	—	MHz	V_{CE}=−12V, I_E=2mA, f=100MHz*
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	−0.5	V	I_C/I_B=−10mA/−1mA

*Transition frequency of the device.

(94S-389-A41)

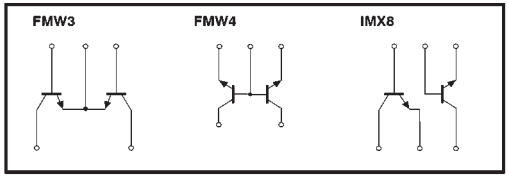
General purpose (dual transistors)

FMW3 / FMW4 / IMX8

●**Features**

1) Two 2SC3906K chips in an SMT package.
2) High breakdown voltage.

●**Circuit diagrams**



●**Absolute maximum ratings** (Ta=25℃)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	120	V	
Collector-emitter voltage	V_{CEO}	120	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current	I_C	50	mA	
Power dissipation	Pc	300 (TOTAL)	mW	*
Junction temperature	Tj	150	℃	
Storage temperature	Tstg	−55～+150	℃	

* 200mW per element must not be exceeded.

●**Package, marking, and packaging specifications**

Part No.	FMW3	FMW4	IMX8
Package	SMT5	SMT5	SMT6
Marking	S3	S4	T4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

●**Electrical characteristics** (Ta=25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	120	—	—	V	I_C=50 μA
Collector-emitter breakdown voltage	BV_{CEO}	120	—	—	V	I_C=1mA
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	I_E=50 μA
Collector cutoff current	I_{CBO}	—	—	0.5	μA	V_{CB}=100V
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	V_{EB}=4V
DC current transfer ratio	h_{FE}	180	—	820	—	V_{CE}=6V, I_C=2mA
Transition frequency	f_T	—	140	—	MHz	V_{CE}=−12V, I_E=2mA, f=100MHz*
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	I_C/I_B=10mA/1mA

*Transition frequency of the device

(94S-398-C41)